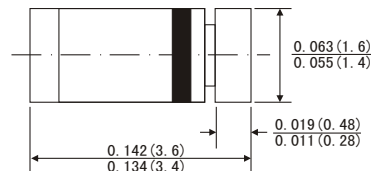


FEATURES

- In MiniMELF case especially for automated insertion
- Standard Zener voltage tolerance is 5%. Add suffix "B" for 2% tolerance
- Other tolerance, non standard and higher zener voltages are upon request
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MiniMELF



MECHANICAL DATA

- Case: MiniMELF(SOD-80) glass case
- Weight: Approx. 0.05 gram

Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES) (TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=25°C	P _{tot}	500 ¹⁾	mW
Junction temperature	T _J	175	°C
Storage temperature range	T _{STG}	-55 to +175	°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

	Symbols	Min	Typ	Max	Units
Thermal resistance junction to ambient	R _{θJA}			300 ¹⁾	K/W
Forward Voltage at I _F = 100mA	V _F			1	V

1) Valid provided that electrodes case is kept at ambient temperature

ZMM1 THRU ZMM200 SILICON PLANAR ZENER DIODES

Type	Zener Voltage range ¹⁾		Maximum zener impedance ¹⁾			Maximum Reverse Leakage Current			Temp Coefficient of zener voltage	
	V _{ZNOM} ³⁾	I _{ZT}		I _{ZT} and I _{ZJK} at I _{ZK}			I _R and I _R ²⁾ at V _R		TK _{vz}	
	V	mA	V	Ω	Ω	mA	μA	μA	V	%/K
ZMM1 ₃₎	0.75	5	0.7...0.8	<8	<50	1	--	--	1.0	-0.26...-0.23
ZMM2.0	2		1.9...2.1	<85	<600		<100	<200		-0.09...-0.06
ZMM2.4	2.4		2.28...2.56	<85	<600		<50	<100		-0.09...-0.06
ZMM2.7	2.7		2.5...2.9	<85	<600		<10	<50		-0.09...-0.06
ZMM3.0	3		2.8...3.2	<85	<600		<4	<40		-0.08...-0.05
ZMM3.3	3.3		3.1...3.5	<85	<600		<2	<40		-0.08...-0.05
ZMM3.6	3.6		3.4...3.8	<85	<600		<2	<40		-0.08...-0.05
ZMM3.9	3.9		3.7...4.1	<85	<600		<2	<40		-0.08...-0.05
ZMM4.3	4.3		4.0...4.6	<75	<600		<1	<20		-0.06...-0.03
ZMM4.7	4.7		4.4...5.0	<60	<600		<0.5	<10		-0.05...+0.02
ZMM5.1	5.1		4.8...5.4	<35	<550		0.1	<2	2	-0.02...+0.02
ZMM5.6	5.6		5.2...6.0	<25	<450					-0.05...+0.05
ZMM6.2	6.2		5.8...6.6	<10	<200					0.03...0.06
ZMM6.8	6.8		6.4...7.2	<8	<150					0.03...0.07
ZMM7.5	7.5		7.0...7.9	<7	<50					0.03...0.08
ZMM8.2	8.2		7.7...8.7	<7	<50					0.03...0.09
ZMM9.1	9.1		8.5...9.6	<10	<50					0.03...0.1
ZMM10	10		9.4...10.6	<15	<70					0.03...0.11
ZMM11	11		10.4...11.6	<20	<70					0.03...0.11
ZMM12	12		11.4...12.7	<20	<90					0.03...0.11
ZMM13	13	12.4...14.1	<26	<110	0.03...0.11					
ZMM15	20	13.8...15.6	<30	<110	0.03...0.11					
ZMM16	15	15.3...17.1	<40	<170	0.03...0.11					
ZMM18	22	16.8...19.1	<50	<170	0.03...0.11					
ZMM20	16	18.8...21.2	<55	<220	0.03...0.11					
ZMM22	24	20.8...23.3	<55	<220	0.04...0.12					
ZMM24	27	22.8...25.6	<80	<220	0.04...0.12					
ZMM27	18	25.1...28.9	<80	<220	0.04...0.12					
ZMM30	30	28...32	<80	<220	0.04...0.12					
ZMM33	33	31...35	<80	<220	0.04...0.12					
ZMM36	36	34...38	<80	<220	0.04...0.12					
ZMM39	39	2.5	37...41	<90	<500	0.25	0.1	<5	0.04...0.12	
ZMM43	43		40...46	<90	<500				0.04...0.12	
ZMM47	47		44...50	<110	<600				0.04...0.12	
ZMM51	51		48...54	<125	<700				0.04...0.12	
ZMM56	56		52...60	<135	<700				0.04...0.12	
ZMM62	62		58...66	<150	<1000				0.04...0.12	
ZMM68	68		64...72	<200	<1000				0.04...0.12	
ZMM75	75		70...79	<250	<1000				0.04...0.12	
ZMM82	82		77...87	<300	<1500				0.05...0.12	
ZMM91	91		85...96	<450	<2000				0.05...0.12	
ZMM100	100	94...106	<450	<5000	0.1	<10	0.05...0.12			
ZMM110	110	104...116	<600	<5000			0.05...0.12			
ZMM120	120	114...127	<800	<5500			0.05...0.12			
ZMM130	130	124...141	<950	<6000			0.05...0.12			
ZMM150	150	138...156	<1250	<6500			0.05...0.12			
ZMM160	160	153...171	<1400	<7000			0.05...0.12			
ZMM180	180	168...191	<1700	<8500			0.05...0.12			
ZMM200	200	188...212	<2000	<10000			0.05...0.12			

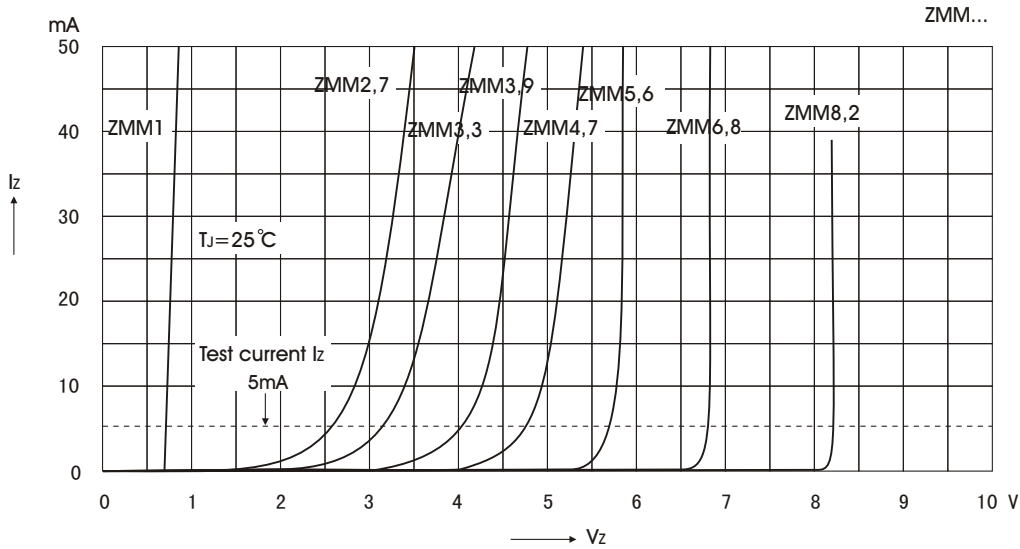
1) Tested with pulse tp=20ms

2) Valid provided that electrodes are kept at ambient temperature

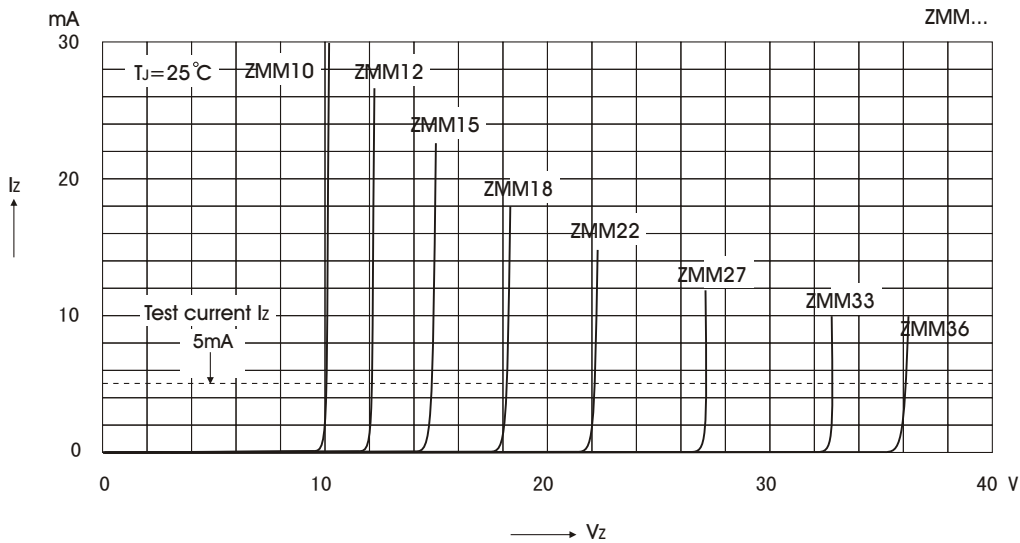
3) The ZMM1 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode to the negative pole.

ZMM1...ZMM200 SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)

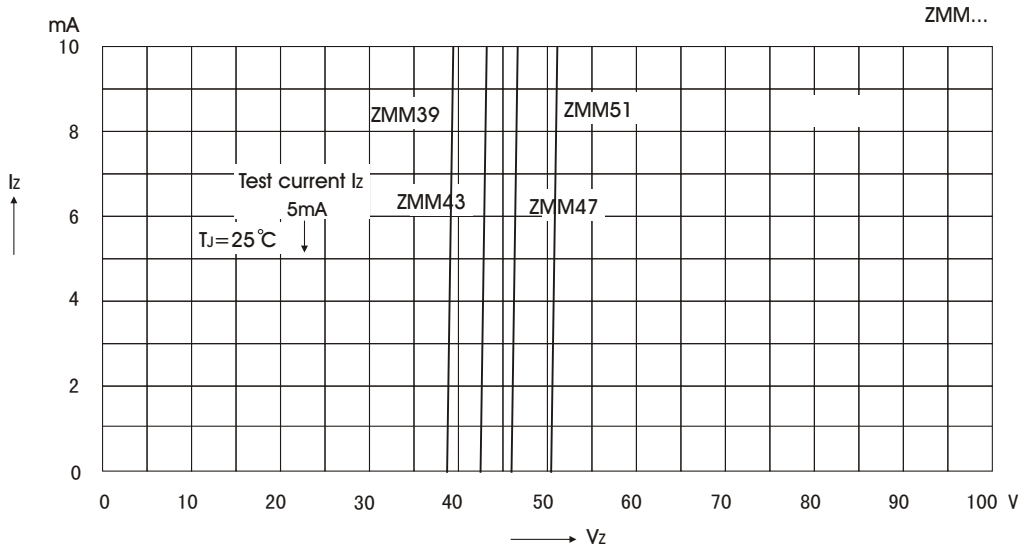


BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)

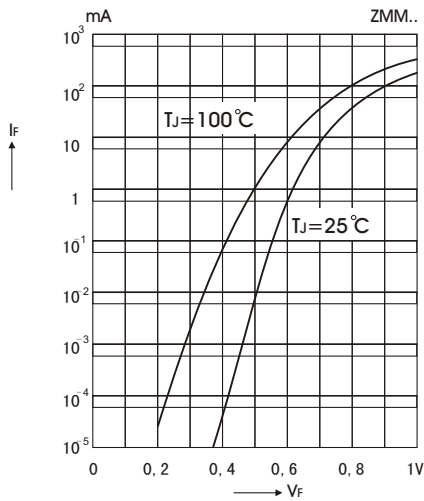


ZMM1...ZMM200 SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)

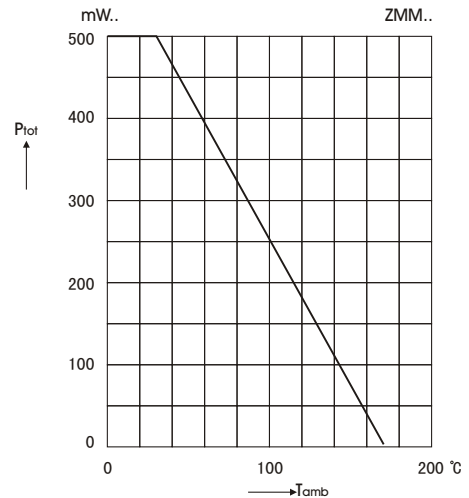


Forward Characteristics



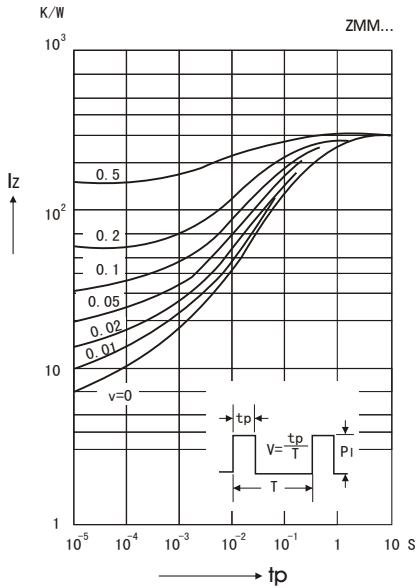
Admissible power dissipation versus ambient temperature

valid provided that electrodes are kept at ambient temperature

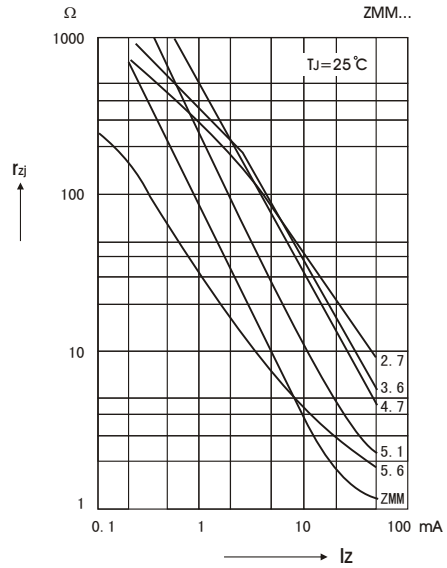


ZMM1...ZMM200 SILICON PLANAR ZENER DIODES

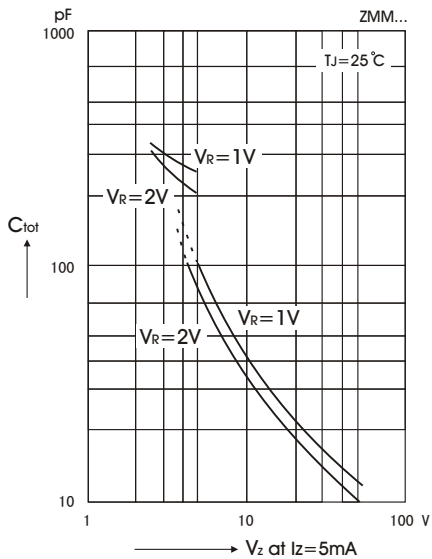
Pulse thermal resistance versus pulse duration



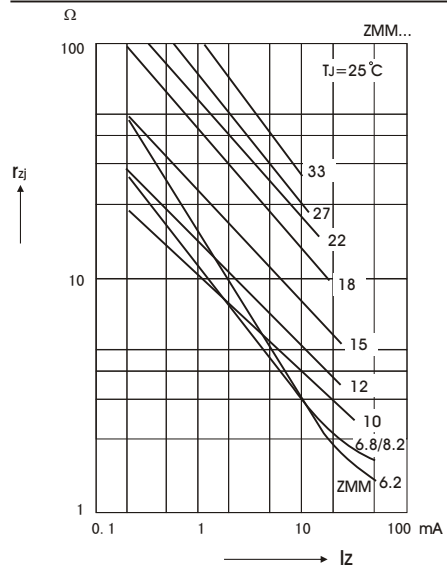
Dynamic resistance versus Zener current



Capacitance versus Zener voltage

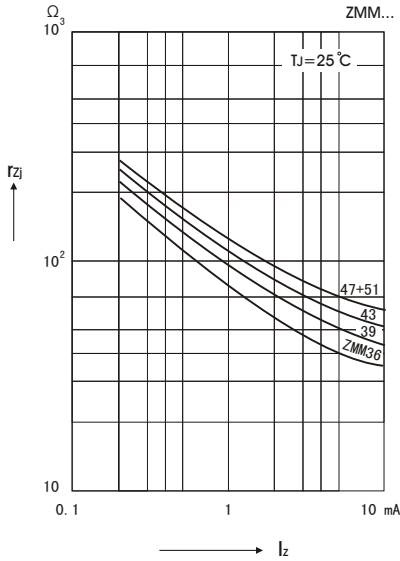


Dynamic resistance versus Zener current

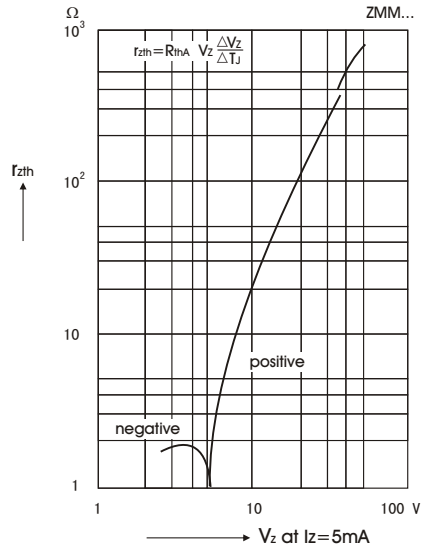


ZMM1...ZMM200 SILICON PLANAR ZENER DIODES

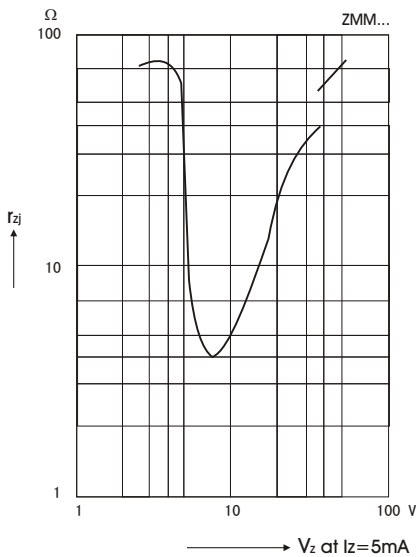
Dynamic resistance versus Zener current



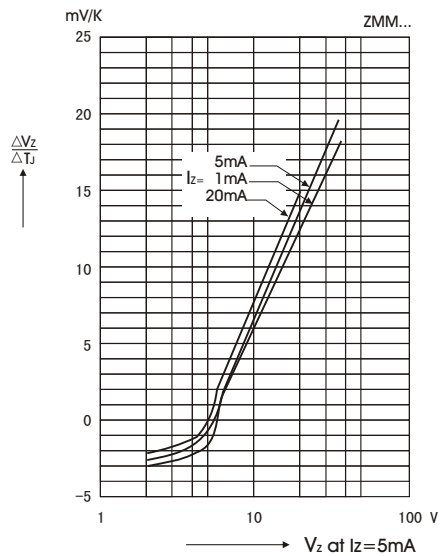
Thermal differential resistance versus Zener voltage



Dynamic resistance versus Zener voltage

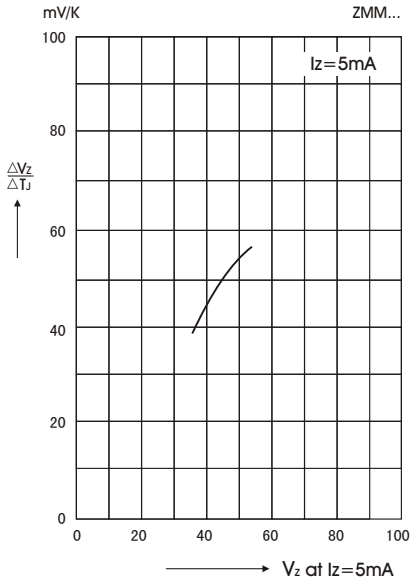


Temperature dependence of Zener voltage versus voltage



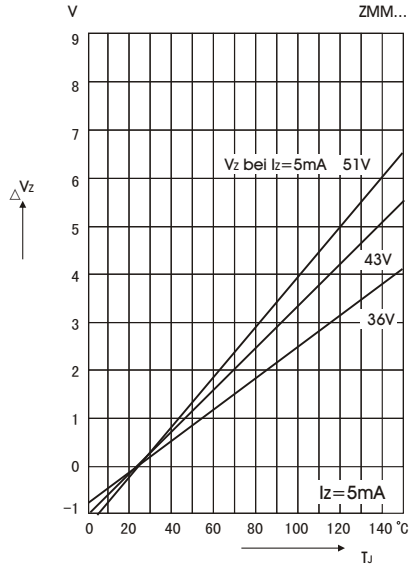
ZMM1...ZMM200 SILICON PLANAR ZENER DIODES

Temperature dependence of Zener voltage versus voltage

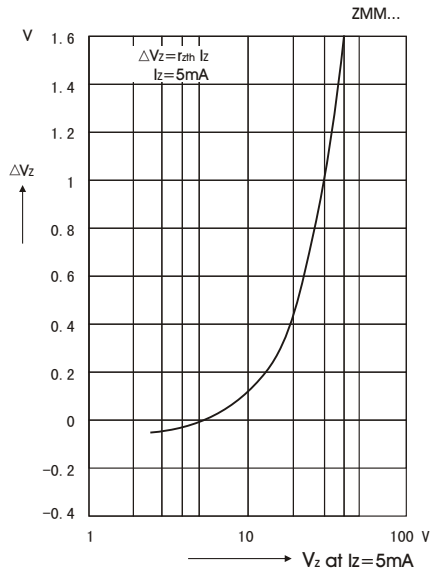
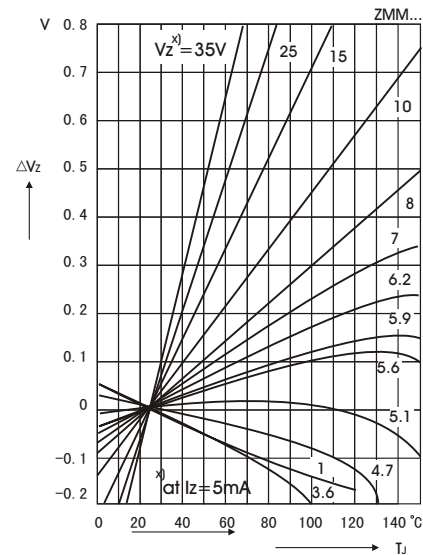


Change of Zener voltage versus junction temperature

Change of Zener voltage versus junction temperature



Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage



ZMM1...ZMM200 SILICON PLANAR ZENER DIODES

Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage

